

24th RD50 Workshop (Bucharest)

Wednesday 11 June 2014

Session 1 - Defect and Material Characterization (09:00 - 13:00)

-Conveners: Ioana Pintilie

time	[id] title	presenter
09:00	[38] Workshop opening	Dr ENCULESCU, Ionut
09:05	[15] Workshop opening	Dr PINTILIE, Ioana MOLL, Michael
09:10	[2] Investigation of point and extended defects in electron irradiated silicon – dependence on the particle energy	RADU, Roxana
09:30	[18] Effect of background impurities and electronic excitation on the behavior of radiation induced interstitial boron complexes	MAKARENKO, Leonid
09:50	[4] A _{Si} -Si _i defect as possible origin of electronically activated degradation of boron and indium doped silicon	Dr LAUER, Kevin
10:10	[8] Electron Induced Damage in Silicon - TRIM and TCAS Simulations	Prof. LINDSTROEM, Gunnar
10:30	Coffee	
11:00	[5] Modelling Vacancy-Interstitial Clusters and their effect on on Carrier Transport in Silicon	Dr ZASINAS, Ernestas
11:20	[27] ESR investigation of paramagnetic point defects in O doped crystalline Si-FZ irradiated with 27 MeV electrons	NISTOR, S.V.
11:40	[28] High resolution transmission electron microscopy (HRTEM) investigations of silicon irradiated with high energy electrons	NISTOR, Leona
12:00	[23] Discussion: Defect and Material Characterization	Dr PINTILIE, Ioana